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# NTB6411AN, NTP6411AN, NVB6411AN



ON Semiconductor®

<http://onsemi.com>

## N-Channel Power MOSFET 100 V, 77 A, 14 mΩ

### Features

- Low  $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ Unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DSS}$	100	V
Gate-to-Source Voltage – Continuous			$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	77	A
		$T_C = 100^\circ\text{C}$		54	
Power Dissipation $R_{\theta JC}$	Steady State	$T_C = 25^\circ\text{C}$	$P_D$	217	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$		$I_{DM}$	285	A
Operating Junction and Storage Temperature Range			$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)			$I_S$	77	A
Single Pulse Drain-to-Source Avalanche Energy ( $V_{DD} = 50 \text{ Vdc}$ , $V_{GS} = 10 \text{ Vdc}$ , $I_{L(pk)} = 56 \text{ A}$ , $L = 0.3 \text{ mH}$ , $R_G = 25 \Omega$ )			$E_{AS}$	470	mJ
Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds			$T_L$	260	$^\circ\text{C}$

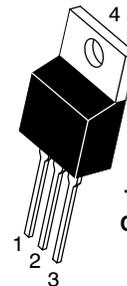
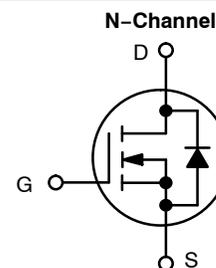
### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State	$R_{\theta JC}$	0.69	$^\circ\text{C/W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	33	

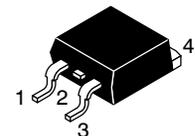
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$ (Note 1)
100 V	14 mΩ @ 10 V	77 A

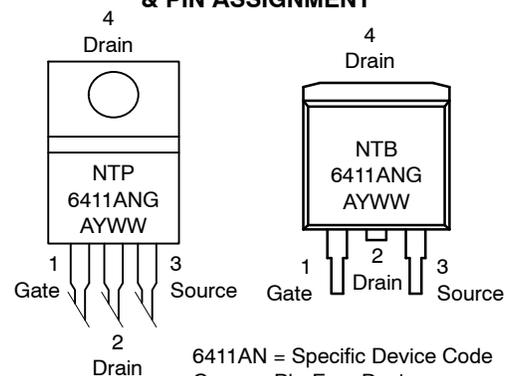


TO-220AB  
CASE 221A  
STYLE 5



D<sup>2</sup>PAK  
CASE 418B  
STYLE 2

### MARKING DIAGRAM & PIN ASSIGNMENT



6411AN = Specific Device Code  
G = Pb-Free Device  
A = Assembly Location  
Y = Year  
WW = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NTB6411AN, NTP6411AN, NVB6411AN

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C Unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			113		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V	T <sub>J</sub> = 25°C		1.0	μA
			T <sub>J</sub> = 125°C		100	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA

## ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	2.0		4.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(th)</sub> /T <sub>J</sub>			8.6		mV/°C
Drain-to-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 72 A		12.7	14	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 10 A		24		S

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		3700		pF
Output Capacitance	C <sub>oss</sub>			550		
Reverse Transfer Capacitance	C <sub>rss</sub>			200		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 80 V, I <sub>D</sub> = 72 A		100		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			4.0		
Gate-to-Source Charge	Q <sub>GS</sub>			16		
Gate-to-Drain Charge	Q <sub>GD</sub>			47		
Plateau Voltage	V <sub>GP</sub>			5.2		
Gate Resistance	R <sub>G</sub>			3.1		Ω

## SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 10 V (Note 3)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DD</sub> = 80 V, I <sub>D</sub> = 72 A, R <sub>G</sub> = 6.2 Ω		16		ns
Rise Time	t <sub>r</sub>			144		
Turn-Off Delay Time	t <sub>d(off)</sub>			107		
Fall Time	t <sub>f</sub>			157		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 72 A	T <sub>J</sub> = 25°C		0.92	1.3	V
			T <sub>J</sub> = 125°C		0.86		
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 72 A, di <sub>S</sub> /dt = 100 A/μs		94		ns	
Charge Time	t <sub>a</sub>			64			
Discharge Time	t <sub>b</sub>			30			
Reverse Recovery Charge	Q <sub>RR</sub>			330			nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

NTB6411AN, NTP6411AN, NVB6411AN

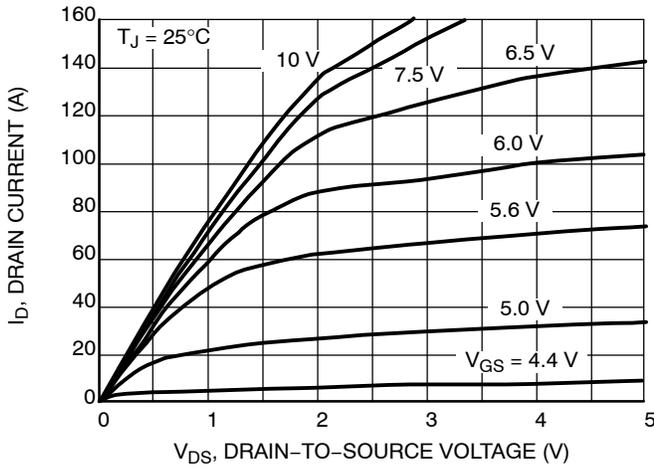


Figure 1. On-Region Characteristics

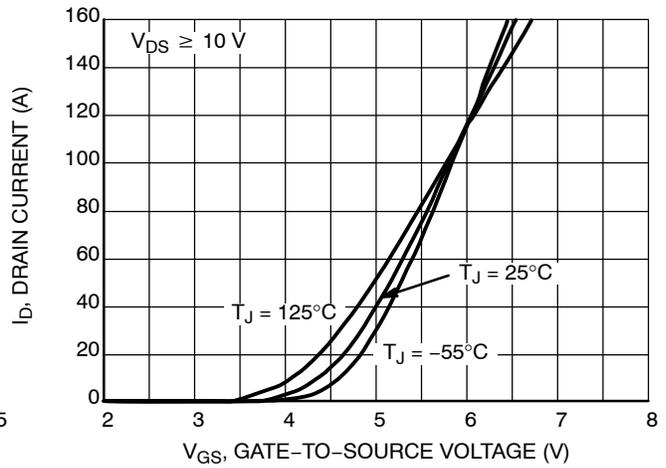


Figure 2. Transfer Characteristics

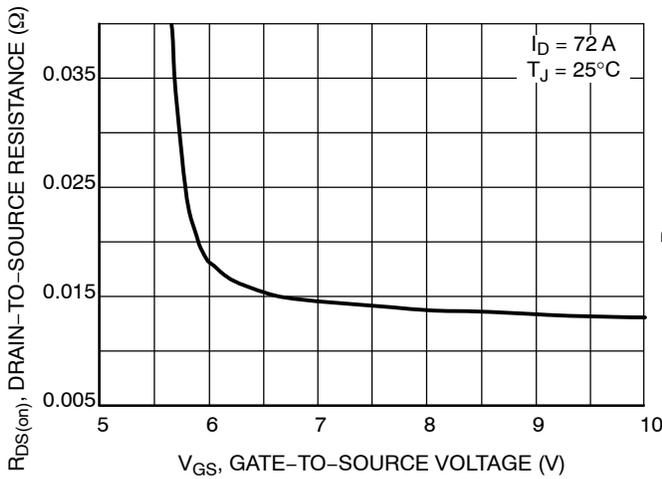


Figure 3. On-Region versus Gate Voltage

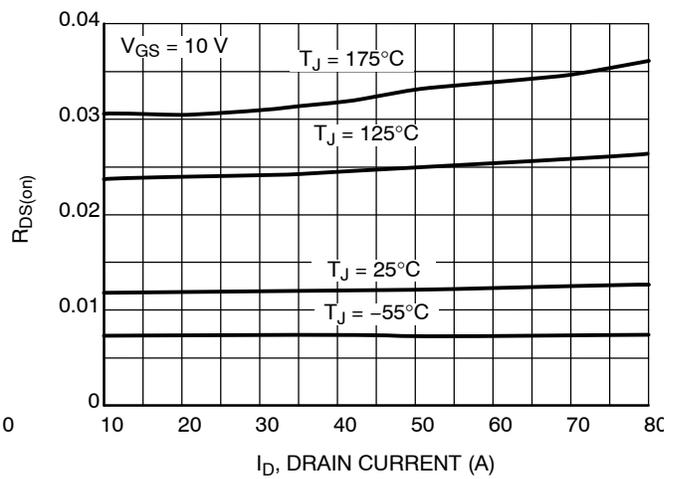


Figure 4. On-Resistance versus Drain Current and Temperature

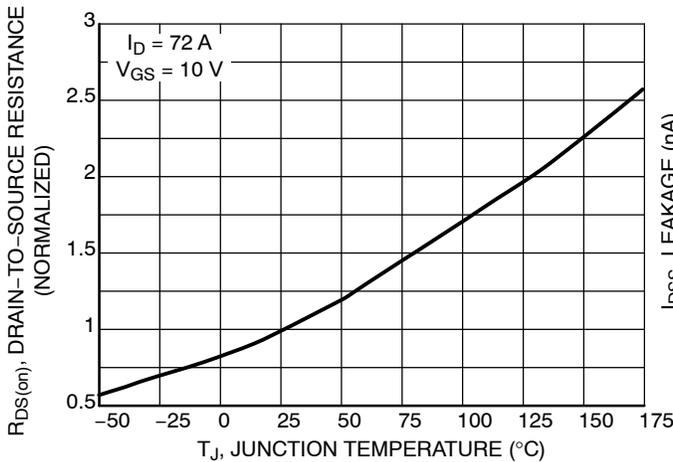


Figure 5. On-Resistance Variation with Temperature

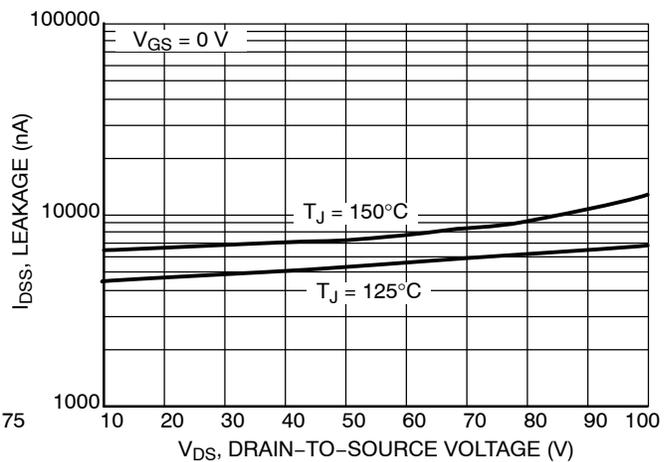


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTB6411AN, NTP6411AN, NVB6411AN

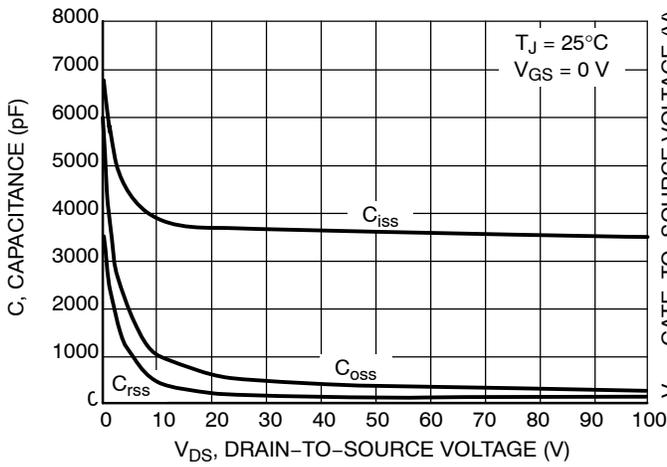


Figure 7. Capacitance Variation

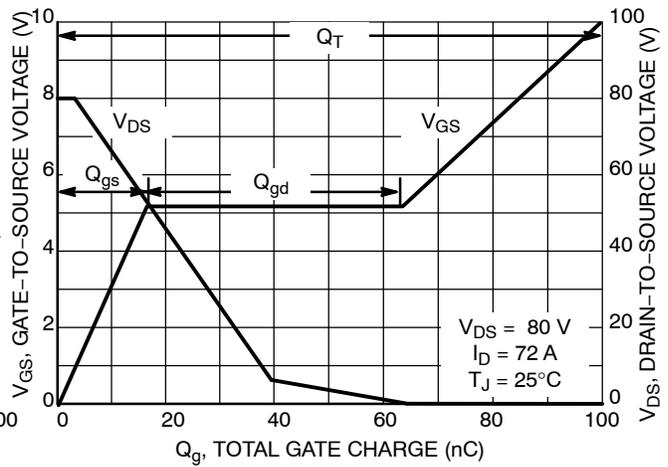


Figure 8. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

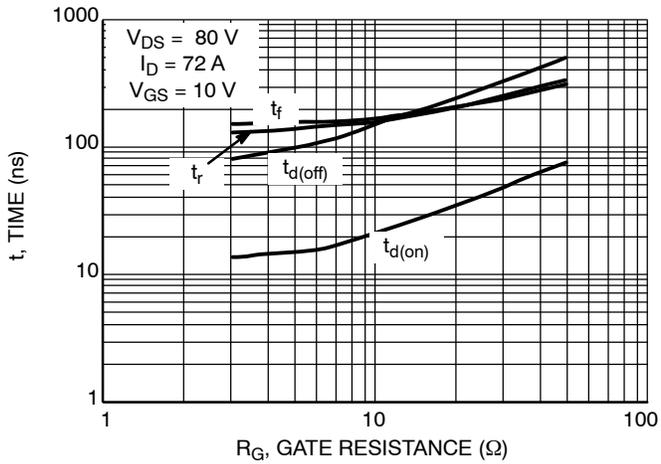


Figure 9. Resistive Switching Time Variation versus Gate Resistance

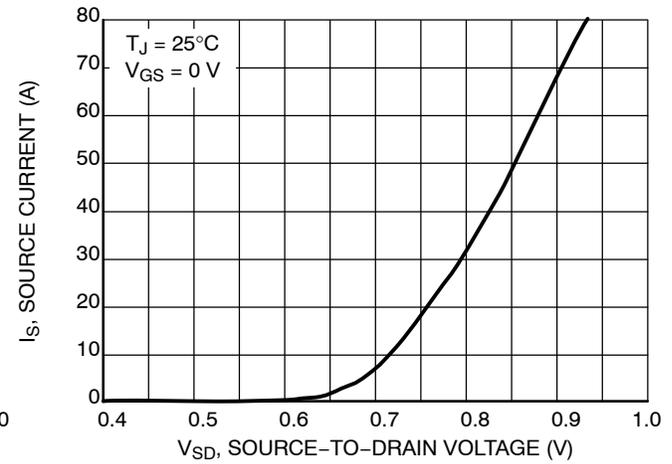


Figure 10. Diode Forward Voltage versus Current

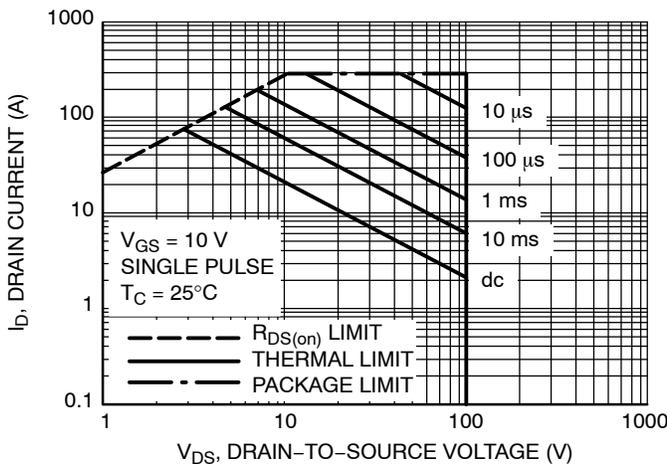


Figure 11. Maximum Rated Forward Biased Safe Operating Area

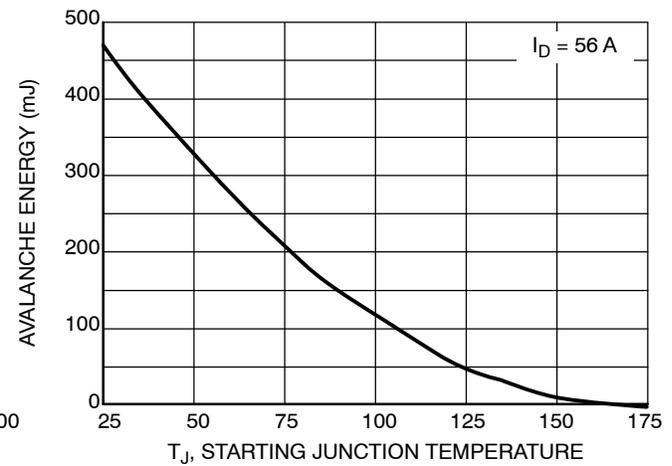
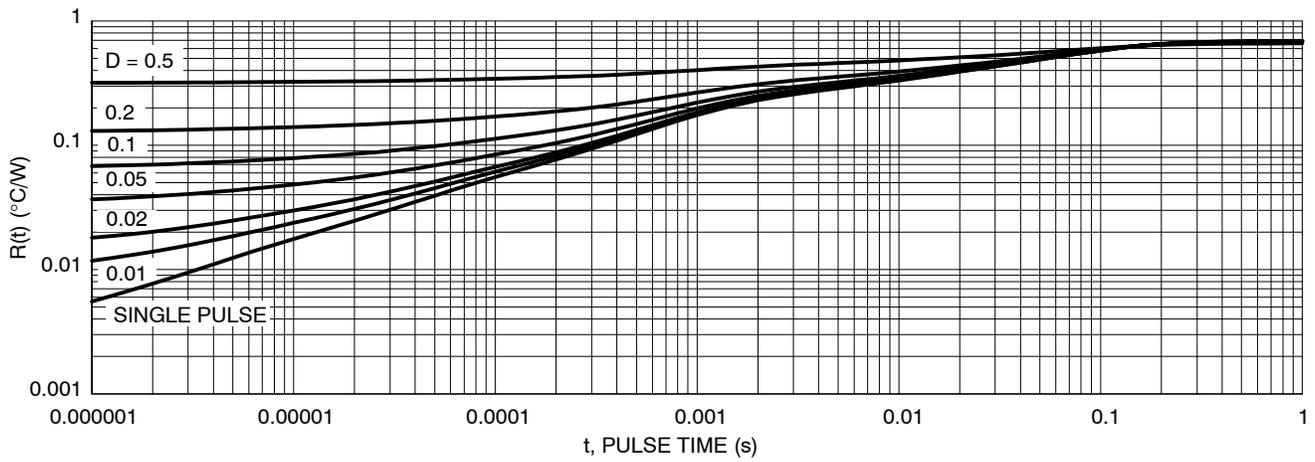


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

# NTB6411AN, NTP6411AN, NVB6411AN



**Figure 13. Thermal Response**

## ORDERING INFORMATION

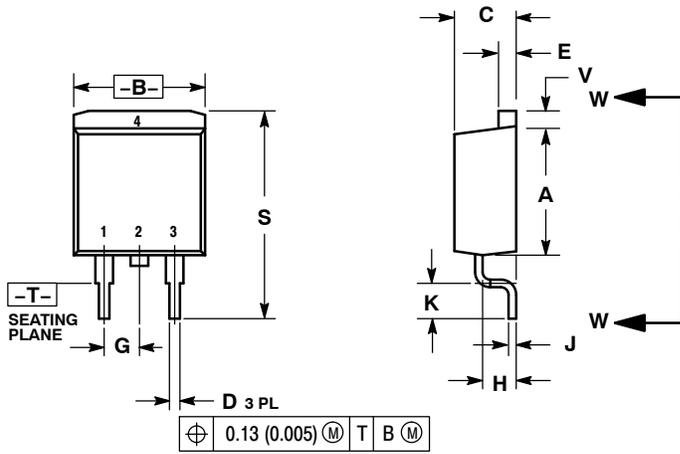
Device	Package	Shipping <sup>†</sup>
NTB6411ANG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTB6411ANT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel
NTP6411ANG	TO-220 (Pb-Free)	50 Units / Rail
NVB6411ANT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTB6411AN, NTP6411AN, NVB6411AN

## PACKAGE DIMENSIONS

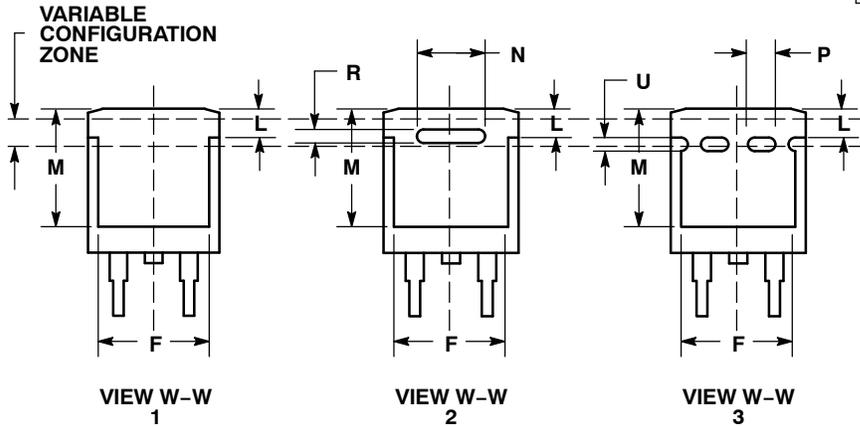
D<sup>2</sup>PAK 3  
CASE 418B-04  
ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

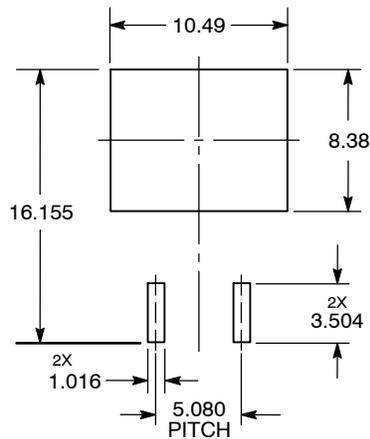
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

### SOLDERING FOOTPRINT\*



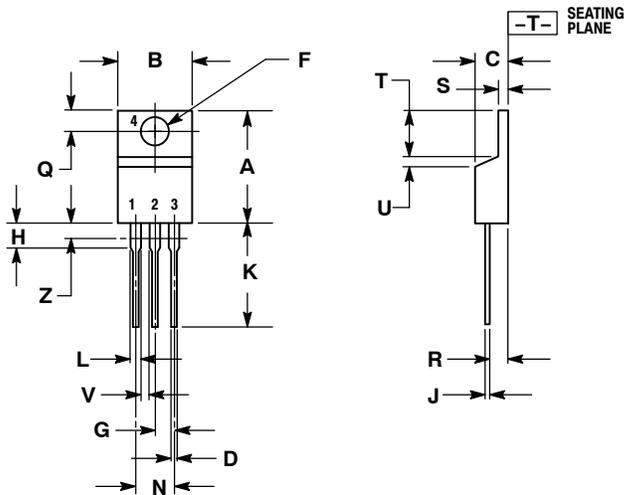
DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NTB6411AN, NTP6411AN, NVB6411AN

## PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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